

Jürgen Blasing

List of Publications by Year in descending order

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Version: 2024-02-01

8
papers

235
citations

1307594

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h-index

1588992

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docs citations

8
times ranked

488
citing authors

#	ARTICLE	IF	CITATIONS
1	Band gap renormalization and Burstein-Moss effect in silicon- and germanium-doped wurtzite GaN up to 10^{20} cm ⁻³ . Physical Review B, 2014, 90, .	3.2	133
2	Anisotropy of effective electron masses in highly doped nonpolar GaN. Applied Physics Letters, 2013, 103, .	3.3	33
3	Ge as a surfactant in metal-organic vapor phase epitaxy growth of a-plane GaN exceeding carrier concentrations of 10^{20} cm ⁻³ . Applied Physics Letters, 2013, 103, .	3.3	18
4	Fast, micrometer scale characterization of group-III nitrides with laboratory X-ray diffraction. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2009, 524, 82-88.	5.6	17
5	Growth and characterization of stacking fault reduced GaN (1,0,ar{1},3) on sapphire. Journal Physics D: Applied Physics, 2013, 46, 125308.	2.8	12
6	Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. Journal of Crystal Growth, 2016, 440, 6-12.	1.5	11
7	Epitaxial growth of highly textured ZnO thin films on Si using an AlN buffer layer by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 032401.	2.1	7
8	The impurity size-effect and phonon deformation potentials in wurtzite GaN. Semiconductor Science and Technology, 2020, 35, 095033.	2.0	4